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Complete if Known

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First Named Inventor	Petti, Christopher
Group Art Unit	Unknown 2818
Examiner Name	Unknown Andy Humphreys

Sheet 1 of 1

Attorney Docket No: MA-109

US PATENT DOCUMENTS

Examiner Initial *	Cite No	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
AL	A1	10/185507		Vyvoda et al.	—	—	06/27/2002
	A2	10/326470		Herner et al.	—	—	12/19/2002
	A3	10/440882		Vyvoda	—	—	05/19/2003
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	A5	6,034,882	03/07/2000	Johnson et al.	—	—	—
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AL	A9	CHIANG, STEVE., et al. "Antifuse Structure Comparison for Field Programmable Gate Arrays", IEDM 92-611, (4/1992), 24.6.1-24.6.4	
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EXAMINER

Andy Humphreys

DATE CONSIDERED

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Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. † Applicant's unique citation designation number (optional) ‡ Applicant is to place a check mark here if English language Translation is attached